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Amdt B
D. Smith-Logan
1-22-03
500.40010X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: K. OHNISHI, et al.
APPLICATION NO.: 09/829,969
FILED: April 11, 2001
FOR: SEMICONDUCTOR DEVICE AND PROCESS FOR PRODUCING THE SAME
ART UNIT: 2818
EXAMINER: Tran

RECEIVED
DEC 27 2002
TECHNOLOGY CENTER 2800

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

December 26, 2002

Sir:

In response to the further Office Action dated September 26, 2002, the

01/29/2003 01 FC:1201 84.00 CH
02 FC:1202 144.00 CH
The following amendments and remarks are respectfully submitted in connection with the above identified application.

IN THE CLAIMS:

Please insert additional Claims 33 - 40, as follows:

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33. A semiconductor device comprising, on a substrate, at least one MOS transistor, wherein a gate electrode of the MOS transistor is provided as a stacked structure comprising a silicon layer, a metal silicide layer, a reaction barrier layer and a metallic layer, formed in that order beginning with the silicon layer.